VHF Transistor

NPN Silicon

Features

• Pb–Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	20	Vdc
Collector-Base Voltage	V _{CBO}	30	Vdc
Emitter-Base Voltage	V _{EBO}	3.0	Vdc
Collector Current – Continuous	Ι _C	100	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

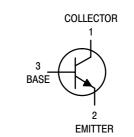
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	R_{\thetaJA}	200	°C/W
Thermal Resistance, Junction–to–Case	$R_{ extsf{ heta}JC}$	83.3	°C/W

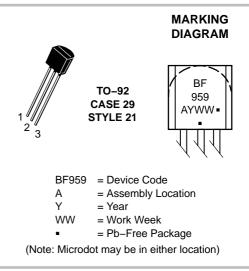
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



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ORDERING INFORMATION

Device	Package	Shipping [†]
BF959	TO-92	5000 Units/Box
BF959G	TO–92 (Pb–Free)	5000 Units/Box
BF959RL1	TO-92	2000/Tape & Reel
BF959RL1G	TO–92 (Pb–Free)	2000/Tape & Reel
BF959ZL1	TO-92	2000/Ammo Pack
BF959ZL1G	TO–92 (Pb–Free)	2000/Ammo Pack

+For information on tape and reel specifications,

including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

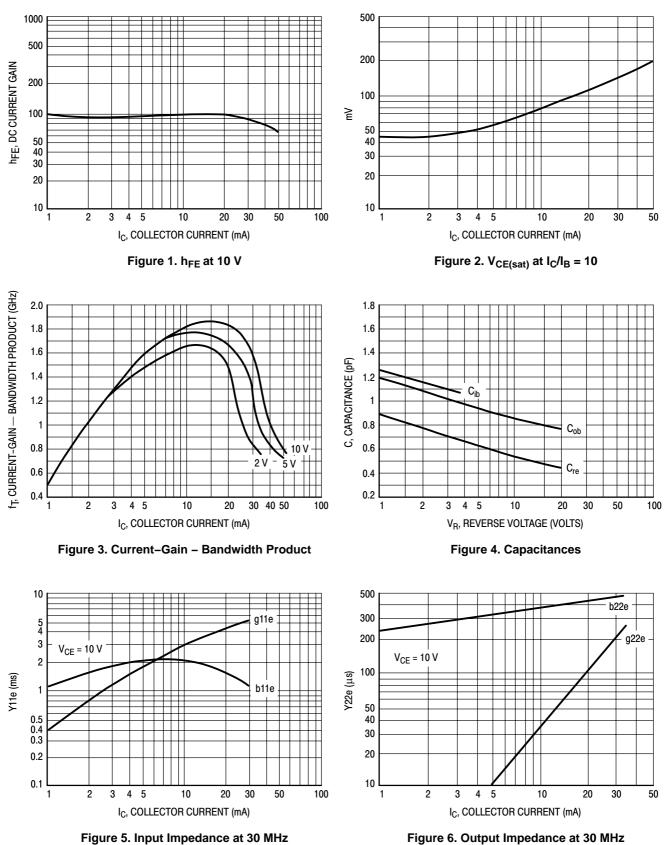
*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

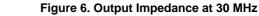
BF959

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS				•	-
Collector – Emitter Breakdown Voltage ($I_C = 1.0 \text{ mAdc}, I_B = 0$)	V _{(BR)CEO}	20	-	-	Vdc
Collector – Base Breakdown Voltage ($I_C = 10 \ \mu Adc$, $I_E = 0$)	V _{(BR)CBO}	30	-	-	Vdc
Emitter – Base Breakdown Voltage ($I_E = 10 \ \mu Adc$, $I_C = 0$)	V _{(BR)EBO}	3.0	-	-	Vdc
Collector Cutoff Current ($V_{CB} = 20$ Vdc, $I_E = 0$)	I _{CBO}	-	-	100	nAdc
ON CHARACTERISTICS	·				
DC Current Gain ($I_C = 5.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$) ($I_C = 20 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$)	h _{FE}	35 40			-
Collector – Emitter Saturation Voltage (I_C = 30 mAdc, I_B = 2.0 mAdc)	V _{CE(sat)}	-	-	1.0	Vdc
Base – Emitter Saturation Voltage ($I_C = 30$ mAdc, $I_B = 2.0$ mAdc)	V _{BE(sat)}	-	-	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS	·	•			
$\label{eq:current-Gain-Bandwidth Product} \begin{aligned} &(I_C = 20 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, \text{ f} = 100 \text{ MHz}) \\ &(I_C = 30 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, \text{ f} = 100 \text{ MHz}) \end{aligned}$	f _T	700 600			MHz
Common Emitter Feedback Capacitance $(V_{CB} = 10 \text{ Vdc}, P_f = 0, f = 10 \text{ MHz})$	C _{re}	-	0.65	-	pF
Noise Figure (I _C = 4.0 mA, V _{CE} = 10 V, R _S = 50 Ω , f = 200 MHz)	N _f	-	3.0	-	dB

BF959

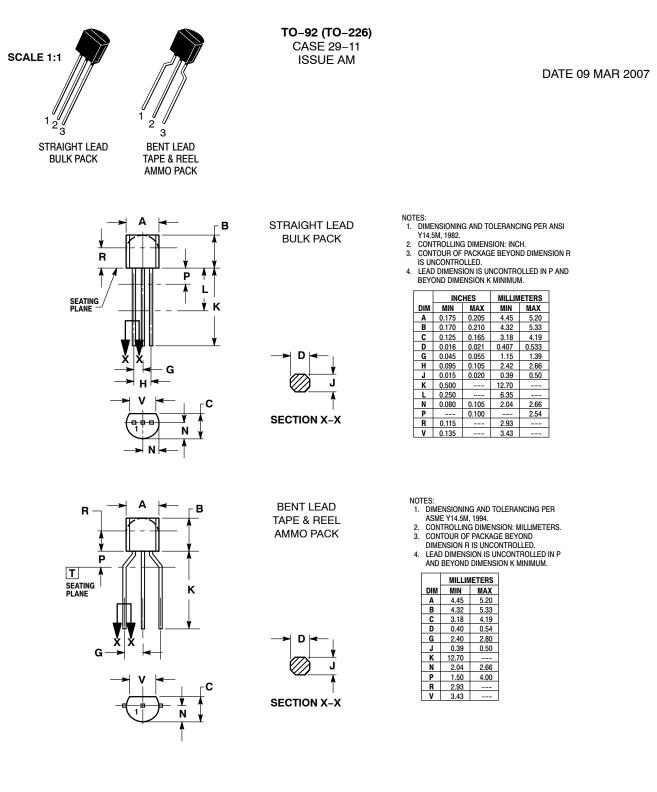




MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

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STYLES ON PAGE 2

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TO-92 (TO-226) CASE 29-11 ISSUE AM

DATE 09 MAR 2007

STYLE 1: PIN 1. EMITTER 2. BASE 3. COLLECTOR STYLE 6: PIN 1. GATE 2. SOURCE & SUBSTRATE 3. DRAIN STYLE 11: PIN 1. ANODE 2. CATHODE & ANODE 3. CATHODE STYLE 16: PIN 1. ANODE 2. GATE 3. CATHODE STYLE 21: PIN 1. COLLECTOR 2. EMITTER 3. BASE STYLE 22: PIN 1. VCC 2. GROUND 2 3. OUTPUT STYLE 31: PIN 1. GATE 2. DRAIN 3. SOURCE

	BASE EMITTER COLLECTOR
2.	Source Drain Gate
2.	MAIN TERMINAL 1 Gate Main Terminal 2
2.	COLLECTOR BASE EMITTER
2.	SOURCE GATE DRAIN

2.	ANODE ANODE CATHODE
	DRAIN GATE SOURCE & SUBSTRATE
2.	ANODE 1 GATE CATHODE 2
2.	ANODE CATHODE NOT CONNECTED
	GATE SOURCE DRAIN
2.	CATHODE ANODE GATE
STYLE 33: PIN 1. 2.	RETURN

3. OUTPUT

2.	CATHODE CATHODE ANODE
2.	BASE 1 EMITTER BASE 2
2.	EMITTER COLLECTOR BASE
	GATE ANODE CATHODE
2.	EMITTER COLLECTOR/ANODE CATHODE
2.	NOT CONNECTED ANODE CATHODE

STYLE 5: PIN 1. DRAIN 2. SOURCE 3. GATE 2. GATE 2. GATE 3. ANODE STYLE 15: PIN 1. CATHODE 2. CATHODE 3. ANODE 2 STYLE 20: PIN 1. NOT CONNECTED 2. CATHODE 3. ANODE STYLE 25: PIN 1. MT 1 2. GATE 3. MT 2 STYLE 30: PIN 1. DRAIN 2. GATE 3. SOURCE STYLE 35: PIN 1. GATE 3. SOURCE STYLE 35: PIN 1. GATE 3. EMITTER

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